

ELECTRON TUNNELLING STUDY OF HIGH-TEMPERATURE SUPERCONDUCTORS

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TO MY FAMILY

PREFACE

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This dissertation is the result of my own work and includes nothing which is the outcome of work done in collaboration, except where reference or acknowledgement is made in the text. The dissertation is not substantially the same as any that I have submitted for a degree, diploma or other qualification at any other University. I further state that no part of my dissertation has already been or is being concurrently submitted for any such degree, diploma or qualification.

Simon Chandler
August 14, 1993

ABSTRACT

This dissertation describes work carried out between June 1987 and October 1991, in the Low Temperature Physics Group at the Cavendish Laboratory, Cambridge.

The aim of this work was to use electron tunnelling spectroscopy to measure the density of excitation states of the recently discovered high-temperature superconductors. Tunnelling is the most sensitive method for measuring a superconductor's energy gap, and historically has provided important evidence for the microscopic mechanism of superconductivity in conventional metals. It was hoped that electron tunnelling would prove equally successful in revealing the mechanism of superconductivity in these new materials.

Preliminary experiments showed that a thick, degraded surface layer prevented preparation of high-quality tunnel junctions by conventional evaporation techniques. For this reason, apparatus for the formation and fine control of low-temperature point-contact junctions was constructed, together with new measurement electronics and a computer-controlled data-acquisition system.

To test this apparatus, point-contact junctions were formed on conventional superconductors. By increasing pressure of the tip on the sample the junction could be moved from the tunnelling to the metallic regime.

Point-contact measurements were then made on a number of ceramic, single-crystal and thin-film high-temperature superconducting materials; some not previously investigated by tunnelling. Although 'gap-like' structure was occasionally observed, anomalous features (e.g., voltage-dependent background, broadening, large zero-bias conductance) were always present and usually dominated the tunnelling characteristics. These complicate estimation of the energy gap and preclude measurement of more subtle properties such as gap anisotropy or the effective phonon spectrum, α^2F . The origins of these non-ideal features have been much debated in the literature and are reviewed in this dissertation.

In the case of thin films deposited by laser ablation the tunnelling characteristics were dominated by single-electron tunnelling effects (Coulomb gap and staircase structure). The results suggest that the surface region consists of numerous, isolated normal metal particles.

CONTENTS

Chapter 1 Introduction	1
1.1 High-Temperature Superconductors	1
1.2 Electron Tunnelling	3
Chapter 2 Microscopic Theory of Superconductivity	5
2.1 An Attractive Electron–Electron Interaction	5
2.2 Cooper Pairs	7
2.3 BCS Theory	9
2.3.1 The BCS Ground State	10
2.3.2 Single-Particle Excitations from the Ground State	13
2.3.3 Finite Temperatures	18
2.3.4 The Gap Ratio and Strong-Coupling Theory	21
Chapter 3 Ideal Tunnel Junctions	27
3.1 MIM Junctions	28
3.1.1 Transfer of Bloch States	30
3.1.2 Excitation Description of Tunnelling	33
3.2 SIN Junctions	34
3.3 SIS Junctions	41
3.4 ScN Junctions	45
3.5 Inelastic Tunnelling	49
3.6 Indirect Tunnelling	50
3.7 Methods for Estimating the Energy Gap	52
Chapter 4 High-T_c Superconductor Tunnel Junctions	57
4.1 An Overview	57
4.2 The Background Conductance	58
4.2.1 Experimental Observations	58
4.2.2 Barrier Effects	61
4.2.3 Inelastic Tunnelling	65
4.2.4 The Zeller–Giaever Model and Charging Effects	67
4.2.5 Intrinsic Causes for Linear Conductance	71

4.3	Broadening	76
4.3.1	Inhomogeneous Gap	77
4.3.2	Anisotropic Gap	81
4.3.3	Lifetime Broadening	87
4.4	Charging Effects: Coulomb Gaps and Staircases	88
4.5	Surface Layers	92
4.6	$2\Delta/k_B T_c$: The Reduced Gap Value of High- T_c Superconductors	97
4.7	Phonon Effects	101
4.8	Halbritter's Model	102
Chapter 5 Experimental Details: I. Measurement Electronics		105
5.1	A.C. Measurement of Conductance	105
5.1.1	Conductance-Bridge Measurements	108
5.2	D.C. Measurement of Conductance	110
5.2.1	Calibration of Raw Data	111
5.2.2	Numerical Differentiation and Smoothing	115
5.2.3	Additional Features of the D.C. Measurement System	118
5.2.4	Possible Improvements to the D.C. Measurement System	118
Chapter 6 Experimental Details: II. Junction Fabrication		121
6.1	Review of Junction Types	121
6.1.1	Planar Junctions	121
6.1.2	Point-Contact Junctions	123
6.1.3	Break Junctions	125
6.1.4	Scanning Tunnelling Microscopes	125
6.2	Planar Junctions	126
6.3	Point-Contact Junctions	127
6.3.1	Design Requirements	128
6.3.2	Vibration Isolation	128
6.3.3	Fine Control of the Tip-Sample Separation	134
6.3.4	Course Control of the Tip-Sample Separation	142
6.3.5	Positioning the Sample	148
6.3.6	Preparation of the Tunnelling Tip	149
6.3.7	Operation of the Point-Contact Insert	152
6.3.8	Suggested Improvements	153

Chapter 7 Results and Discussion	155
7.1 Conventional Superconductor Point-Contact Junctions	155
7.1.1 Pb SIN Junctions	155
7.1.2 Pb ScN Junctions	160
7.1.3 Nb ScN Junctions	161
7.2 High- T_c Superconductor Planar Junctions	162
7.2.1 $\text{YBa}_2\text{Cu}_3\text{O}_y$ Ceramic	162
7.3 High- T_c Superconductor Point-Contact Junctions	163
7.3.1 $\text{YBa}_2\text{Cu}_3\text{O}_y$ Ceramic	163
7.3.2 Bi-Sr-Ca-Cu-O Single Crystals	171
7.3.3 $(\text{Tl,Pb})(\text{Ca,Pr})\text{Sr}_2\text{Cu}_2\text{O}_y$ Ceramic	176
7.3.4 $\text{YBa}_2\text{Cu}_3\text{O}_y$ Thin Films	182
Chapter 8 Conclusion	193
8.1 Summary	193
8.2 Recommendations for Future Work	194
Appendix A Electronic Circuit Details	197
A.1 Measurement of Conductance–Voltage Characteristics	197
A.1.1 Circuit Design	197
A.1.2 Modulation Broadening	203
A.2 Servo Control of the Tunnelling Tip	204
Appendix B Low-T_c Oxide Superconductors	207
B.1 Bismuthate Superconductors	207
B.2 $\text{Nd}_{2-x}\text{Ce}_x\text{CuO}_{4-y}$	209
References	211